

Form 1449*	Atty. Docket No.: 303.676US5	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Gurtej Singh Sandhu et al.	
	Filing Date: Herewith	Group: <del>Unknown</del> 1775

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**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
ABS	3,900,312	08/19/1975	Terry, J.C., et al.	75	68 B	10/16/72
	4,340,617	07/20/1982	Deutsch, et al.	427	53.1	05/19/80
	4,343,870	08/10/1982	Heller, A., et al.	429	111	09/08/80
	4,359,490	11/16/1982	Lehrer, W.I.	427	95	07/13/81
	4,713,258	12/15/1987	Umemura	427	35	07/03/85
	4,721,631	01/26/1988	Endo, et al.	427	66	03/09/87
	4,751,101	06/14/1988	Joshi, R.V.	427	39	04/30/87
	4,868,005	09/19/1989	Ehrlich, et al.	427	53.1	03/10/88
	4,876,112	10/24/1989	Kaito, et al.	427	38	03/27/87
	4,884,123	11/28/1989	Dixit, P., et al.	357	71	02/19/87
	4,923,717	05/08/1990	Gladfelter, et al.	427	252	03/17/89
	4,957,777	09/18/1990	Ilderem, V., et al.	427	55	10/12/89
	4,971,655	11/20/1990	Stefano, et al.	156	659.1	12/26/89
	5,005,519	04/01/1991	Egermeier, et al.	118	722	03/14/90
	5,015,330	05/14/1991	Okumura, K., et al.	156	643	02/28/90
	5,022,905	06/11/1991	Grundy, et al.	65	60.51	10/12/89
	5,032,233	07/16/1991	Yu, C., et al.	204	192.28	09/05/90
	5,049,975	09/17/1991	Ajika, N., et al.	357	71	03/12/90
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	5,147,819	09/15/1992	Yu, C., et al.	437	173	02/21/91
	5,173,327	12/22/1992	Sandhu, G.S., et al.	427	573	06/18/91
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	5,196,360	03/23/1993	Doan, T.T., et al.	437	41	04/06/92
	5,202,579	04/13/1993	Fujii, H., et al.	257	751	01/21/92
	5,227,331	07/13/1993	Westmoreland, D.	437	174	02/10/92
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	5,232,873	08/03/1993	Geva, M., et al.	437	192	10/13/92
	5,240,739	08/31/1993	Doan, T., et al.	427	126.1	08/07/92
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	5,252,518	10/12/1993	Sandhu, et al.	437	200	03/03/92
	5,254,499	10/19/1993	Sandhu, G., et al.	437	192	07/14/92
	5,258,096	11/02/1993	Sandhu, et al.	156	643	08/20/92
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	5,275,715	01/04/1994	Tuttle	205	123	01/23/92
	5,278,100	01/11/1994	Doan, T.T., et al.	437	200	11/08/91
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	5,320,880	06/14/1994	Sandhu, G.S., et al.	427	578	11/18/93
	5,341,016	08/23/1994	Prall, K.D., et al.	257	412	06/16/93
	5,344,792	09/06/1994	Sandhu, G.S., et al.	437	200	03/04/93
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<u>ABS</u>	5,376,405	12/27/1994	Doan, T., et al.	427	126.1	04/15/93
	5,381,302	01/10/1995	Sandhu, G., et al.	361	305	08/10/93
	5,384,284	01/24/1995	Doan, T.T., et al.	437	190	10/01/93
	5,384,289	01/24/1995	Westmoreland, D.L.	437	245	06/17/93
	5,391,410	02/21/1995	Nii, T., et al.	427	578	05/28/93
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	5,453,640	09/26/1995	Kinoshita, Y.	257	520	12/20/94
	5,459,353	10/17/1995	Kanazawa, M.	257	751	01/05/95
	5,496,762	03/05/1996	Sandhu, et al.	437	60	06/02/94
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	5,508,066	04/16/1996	Akahori, T.	427	571	09/14/94
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	6,120,844	09/19/2000	Chen, L., et al.	427	255.28	03/27/96
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**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
<u>ABS</u>	0798777	10/01/1997	European	H01L	21/768		
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n	Init	Doc	Num	ber	Date	Country	Class	Subclass	Yes	
No										

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	Bouteville, A., et al., "TiSi <sub>2</sub> Selective Growth in a rapid thermal low pressure chemical vapor depositoin system", <u>Journal of the Electrochemical Society</u> , 139, 2260-2263, (August 1992)
	Cowher, M., et al., "Low Temperature CVD Garnet Growth", <u>Journal of Crystal Growth</u> , 46, 399-402, (1979) NO MONTH
	Engqvist, J., et al., "Selective deposition of TiSi <sub>2</sub> from H <sub>2</sub> -TiCl <sub>4</sub> Gas mixtures and si: Aspects of Thermodynamics including Critical evaluation of thermochemical data in the Ti-Si System", <u>Journal of the Electrochemical Society</u> , 139, 3197-3205, (November 1992)
	Esquivel, A., et al., "Electrical and Physical Characteristics of Dry Oxygen, High Pressure Oxidation for SUB-0.5 um CMOS Isolation", <u>Abst. Int'l Electron Devices Meeting</u> , (1994) NO MONTH
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	Lie, L., et al., "High Pressure Oxidation of Silicon in Dry Oxygen", <u>J. Electrochemical Soc. : Solid State Science and Technology</u> , 129, 2828-2834, (Dec. 1982)
	Moeller, T., et al., "Semiconducting Elements, Ch. 30", <u>In: Chemistry with Inorganic Qualitative Analysis</u> , 2nd Edition, Academic Press, 995-996, (1984) NO MONTH
	Morosanu, C., <u>Thin Films by Chemical Vapor Deposition</u> , Elsevier, N.Y., 42-54 & 460-475, (1990) NO MONTH

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	Rosler, R., et al., "Plasma-Enhanced CVD of Titanium Silicide", <u>J. Vacuum Science Tech.</u> , B2(4), 733-737, (October/December 198)
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